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Single Phase Fast Recovery Bridge (Power Modules), 61 A



SOT-227

PRODUCT SUMMARY				
V _{RRM}	600 V			
I ₀	61 A			
t _{rr}	170 ns			
Туре	Modules - Bridge, Fast			
Package	SOT-227			
Circuit	Single phase bridge			

FEATURES







- · Simplified mechanical designs, rapid assembly
- Excellent power/volume ratio
- Designed and qualified for industrial and consumer level
- UL approved file E78996



· Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	CHARACTERISTICS VALUES				
1-		61	Α			
I _O	T _C	57	°C			
I _{FSM}	50 Hz	300	Α			
	60 Hz	310	A			
l ² t	50 Hz	442	A ² s			
	60 Hz	402	A-8			
V _{RRM}		600	V			
T _J		-55 to +150	°C			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS						
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} MAXIMUM AT T _J MAXIMUM mA		
SA61BA60	60	600	700	10		



FORWARD CONDUCTION						
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum DC output current		Resistive or in	ductive load		61	Α
at case temperature	Io				57	°C
		t = 10 ms	No voltage		300	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		310	Α
non-repetitive forward current	I _{FSM}	t = 10 ms	100 % V _{RRM}	Initial T _J = T _J maximum	250	
		t = 8.3 ms	reapplied		260	
		t = 10 ms	No voltage		442	- A ² s
Maximum 12t for fusing	l ² t	t = 8.3 ms	reapplied		402	
Maximum I ² t for fusing	1-1	t = 10 ms	100 % V _{RRM}		313	
		t = 8.3 ms	reapplied		284	
Maximum I ² √t for fusing	I ² √t	I^2t for time $t_x = I_2\sqrt{t} \times \sqrt{t_x}$; $0.1 \le t_x \le 10$ ms, $V_{RRM} = 0$ V			4.4	kA²√s
Value of threshold voltage	V _{F(TO)}	T _J maximum			0.914	V
Forward slope resistance	r _t				10.5	mΩ
Maximum forward voltage drap	W	T _J = 25 °C, I _{FN}	c, I _{FM} = 30 A _{pk}		1.33	
Maximum forward voltage drop	V _{FM}	$T_J = T_J$ maximum, $I_{FM} = 30 A_{pk}$ $t_p = 400 \mu s$		1.23	V	
RMS isolation voltage base plate	V _{ISOL}	f = 50 Hz, t = 1 s			3000	

RECOVERY CHARACTERIS	TICS			
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Reverse recovery time, typical	+	$T_J = 25 ^{\circ}\text{C}, \ I_F = 20 \text{A}, \ V_R = 30 \text{V}, \ dI_F/dt = 100 \text{A/}\mu\text{s}$	170	
neverse recovery time, typical	t _{rr}	$T_J = 125 ^{\circ}\text{C}, I_F = 20 \text{A}, V_R = 30 \text{V},$ $dI_F/dt = 100 \text{A/}\mu\text{s}$	250	ns
Poverse receiver augrent typical	I _{rr}	$T_J = 25 ^{\circ}\text{C}, \ I_F = 20 \text{A}, \ V_R = 30 \text{V}, \ dI_F/dt = 100 \text{A/}\mu\text{s}$	10.5	Α
Reverse recovery current, typical		$T_J = 125 ^{\circ}\text{C}, I_F = 20 \text{A}, V_R = 30 \text{V},$ $dI_F/dt = 100 \text{A/}\mu\text{s}$	16	
Deverse receivery charge, typical	0	$T_J = 25 ^{\circ}\text{C}, \ I_F = 20 \text{A}, \ V_R = 30 \text{V}, \ dI_F/dt = 100 \text{A/}\mu\text{s}$	900	nC
Reverse recovery charge, typical	Q _{rr}	$T_J = 125 ^{\circ}\text{C}$, $I_F = 20 \text{A}$, $V_R = 30 \text{V}$, $dI_F/dt = 100 \text{A/}\mu\text{s}$	1970	no no
Snap factor, typical	S	T _J = 25 °C	0.6	-
Junction capacitance, typical	C _T	V _R = 600 V	67	pF

THERMAL AND MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction and storage temperature range	T _J , T _{Stg}		- 55	-	150	°C
Thermal resistance junction to case	R_{thJC}		-	-	0.30	°C/W
Thermal resistance case to heatsink	R _{thCS}	Flat, greased surface	-	0.05	-	C/VV
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
		Torque to heatsink	=	-	1.3 (11.5)	Nm (lbf.in)
Case style				SOT	-227	

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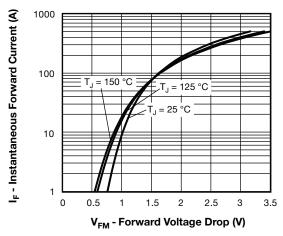


Fig. 1 - Typical Forward Voltage Drop Characteristics

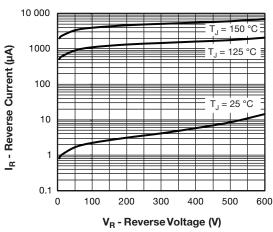


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

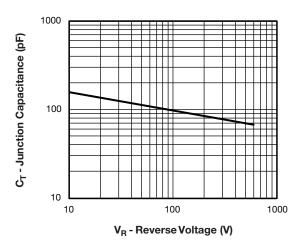


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

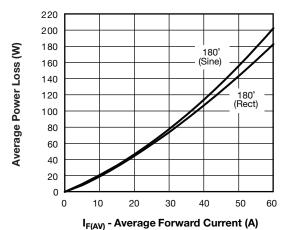


Fig. 4 - Current Rating Characteristics

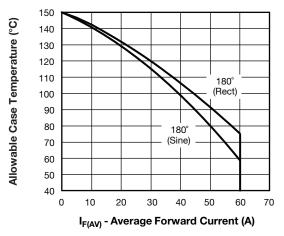


Fig. 5 - Forward Power Loss Characteristics



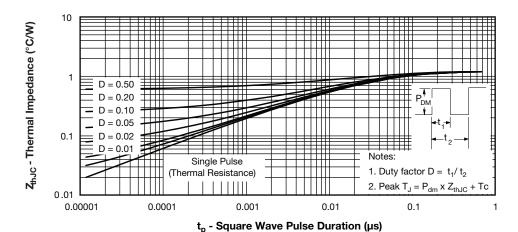


Fig. 6 - Typical Forward Voltage Drop Characteristics

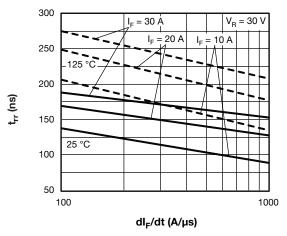


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

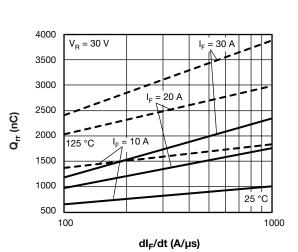


Fig. 8 - Typical Stored Charge vs. dl_F/dt

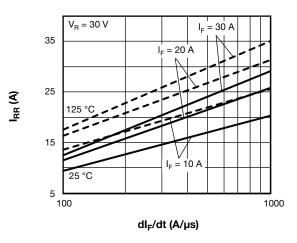


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt

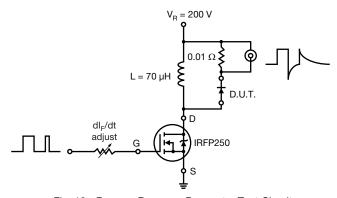
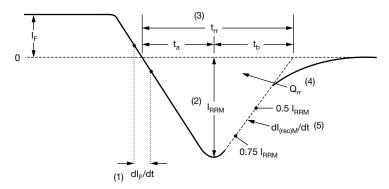


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_F$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

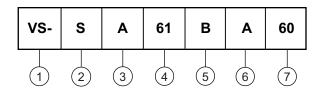
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dI_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - S = Fast recovery diode

3 - A = Present Silicon Generation

4 - Current rating (61 = 61 A)

5 - Circuit configuration:

B = Single phase bridge

6 - Package indicator:

A = SOT-227, standard insulated base

7 - Voltage rating (60 = 600 V)

CIRCUIT CONFIGURATION						
CIRCUIT	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING				
Single phase bridge	В	(AC) 4 0				

LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?95423</u>				
Packaging information	www.vishay.com/doc?95425			



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